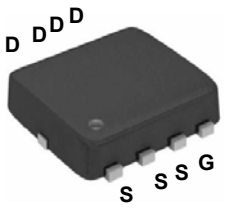
GOOD-ARK
SEMICONDUCTOR

GSFN0956

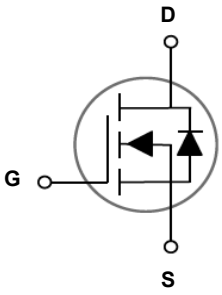
100V N-Channel MOSFET

Main Product Characteristics

$V_{(BR)DSS}$	100V
$R_{DS(ON)}$	115mΩ
I_D	10A



PPAK3X3



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSFN0956 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current – Continuous (T_C=25°C)	I_D	10	A
Drain Current – Continuous (T_C=100°C)		6.3	A
Drain Current – Pulsed[1]	I_{DM}	40	A
Single Pulse Avalanche Energy[2]	E_{AS}	6	mJ
Single Pulse Avalanche Current[2]	I_{AS}	11	A
Power Dissipation (T_C=25°C)	P_D	29.8	W
Power Dissipation – Derate above 25°C		0.24	W/°C
Storage Temperature Range	T_{STG}	-50 to +150	°C
Operating Junction Temperature Range	T_J	-50 to +150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	---	62	°C/W
Thermal Resistance Junction to Case	$R_{\theta JC}$	---	4.2	°C/W

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	100	---	---	V
BV_{DSS} Temperature Coefficient	$\triangle BV_{DSS}/\triangle T_J$	Reference to 25ÁC, I_D=1mA	---	0.09	---	V/ÁC
Drain-Source Leakage Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V, T_J=25ÁC	---	---	1	uA
		V_{DS}=80V, V_{GS}=0V, T_J=125ÁC	---	---	10	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=Ñ20V, V_{DS}=0V	---	---	Ñ100	nA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	---	90	115	mq
		V_{GS}=4.5V, I_D=8A	---	95	120	mq
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D =250uA	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\triangle V_{GS(th)}$		---	-5	---	mV/ÁC
Forward Transconductance	gfs	V_{DS}=10V, I_D=10A	---	8.7	---	S
Dynamic and Switching Characteristics						
Total Gate Charge[3, 4]	Q_g	V_{DS}=50V, V_{GS}=10V, I_D=2A	---	20	40	nC
Gate-Source Charge[3, 4]	Q_{gs}		---	3.2	6	
Gate-Drain Charge[3, 4]	Q_{gd}		---	3.6	7	
Turn-On Delay Time[3, 4]	$T_{d(on)}$	V_{DD}=50V, V_{GS}=10V, R_G=3.3q , I_D=1A	---	18	36	nS
Rise Time[3, 4]	T_r		---	4	8	
Turn-Off Delay Time[3, 4]	$T_{d(off)}$		---	40	80	
Fall Time[3, 4]	T_f		---	3	6	
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, F=1MHz	---	1400	2800	pF
Output Capacitance	C_{oss}		---	60	120	
Reverse Transfer Capacitance	C_{rss}		---	35	70	
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	2	4	q
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	V_G=V_D=0V, Force Current	---	---	10	A
Pulsed Source Current	I_{SM}		---	---	20	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=1A, T_J=25ÁC	---	---	1	V
Reverse Recovery Time[3]	t_{rr}	I_S=1A, dI/dt=100A/Õs, T_J=25ÁC	---	38	---	nS
Reverse Recovery Charge[3]	Q_{rr}		---	27	---	nC

Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=11A, R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≦ 300uS, duty cycle ≦ 2 % .
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

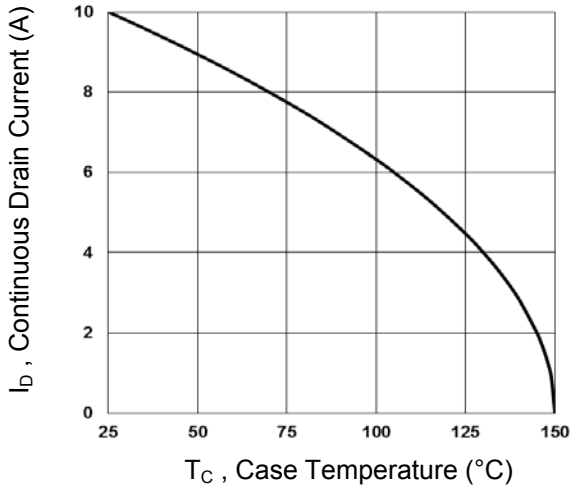


Fig.1 Continuous Drain Current vs. T_C

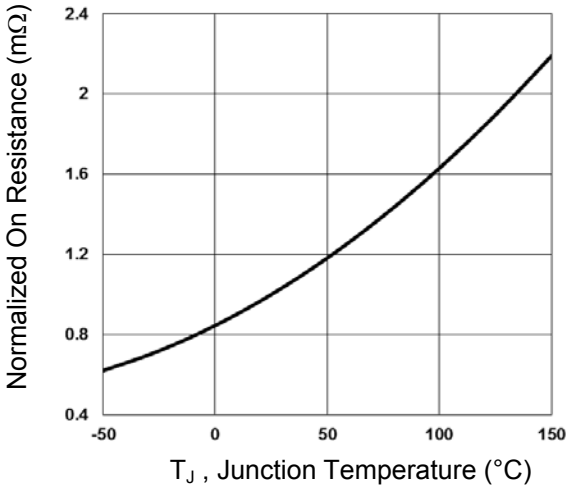


Fig.2 Normalized $R_{DS(ON)}$ vs. T_J

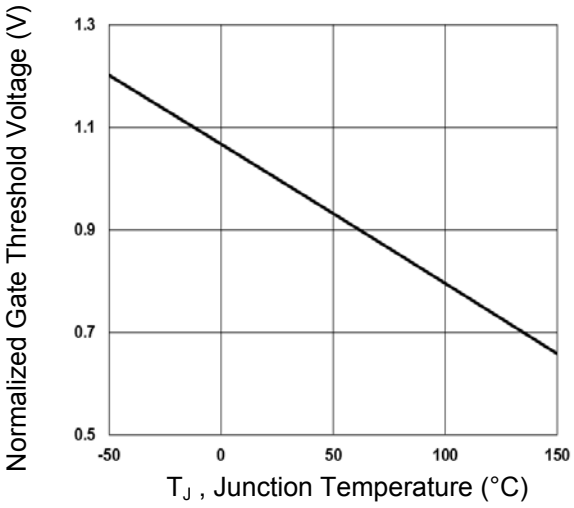


Fig.3 Normalized V_{th} vs. T_J

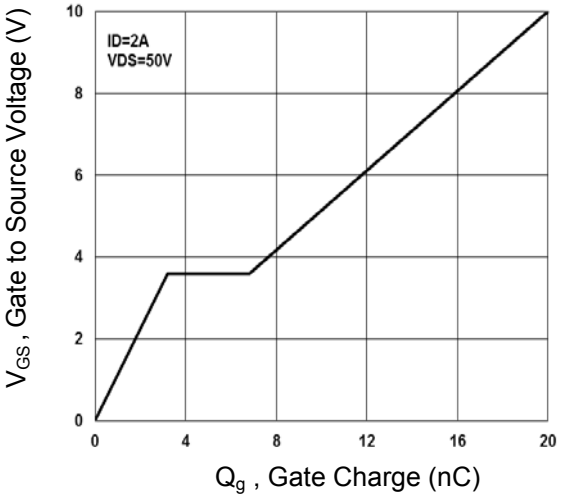


Fig.4 Gate Charge Waveform

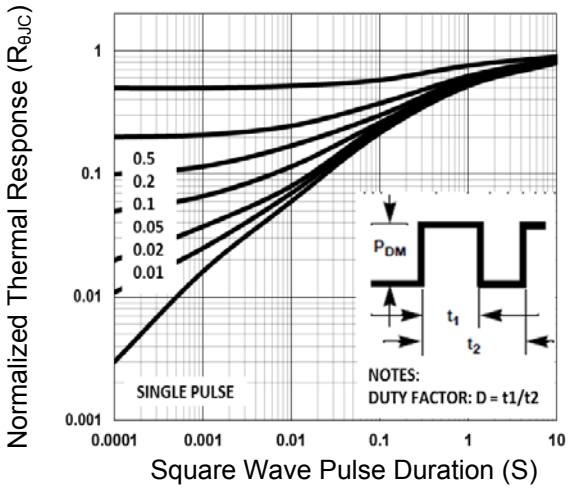


Fig.5 Normalized Transient Impedance

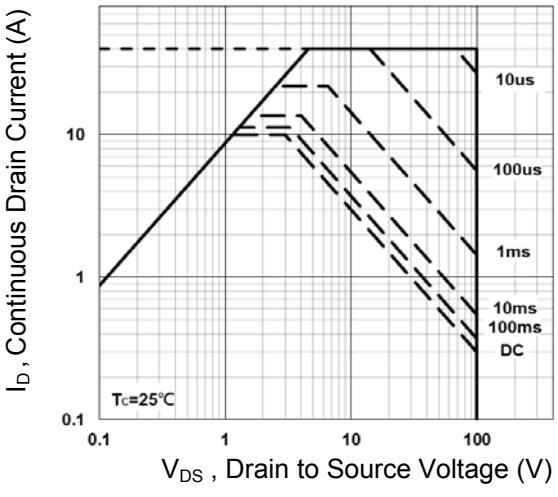


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

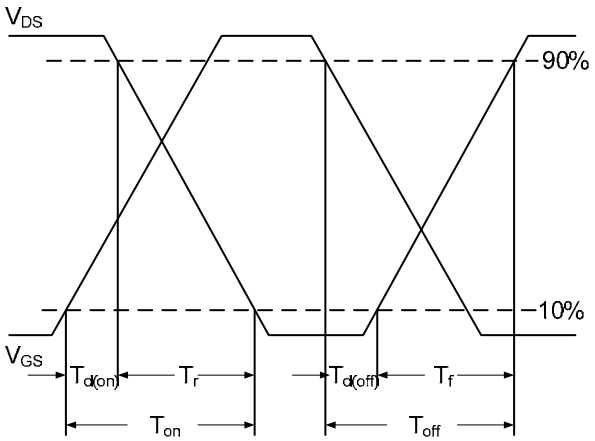


Fig.7 Switching Time Waveform

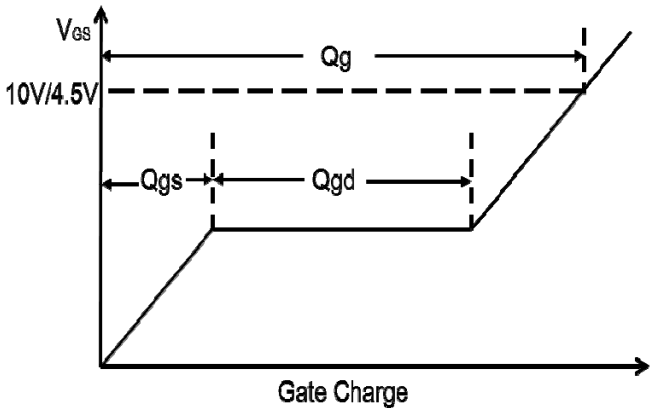
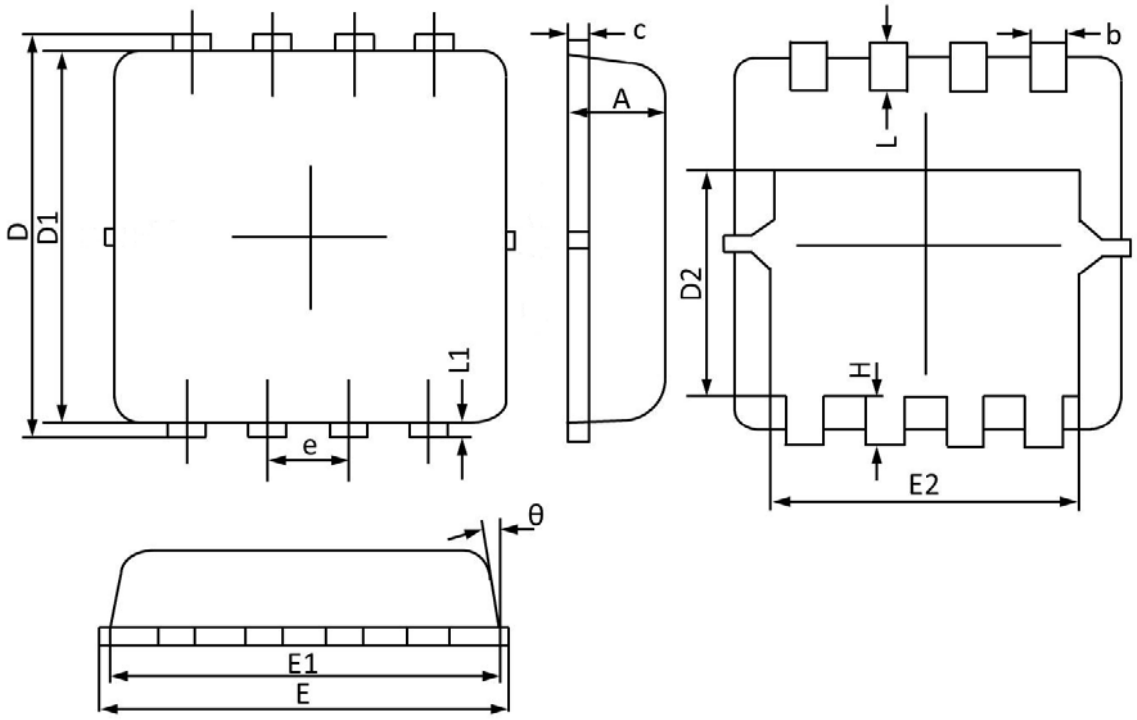


Fig.8 Gate Charge Waveform

Package Outline Dimensions PPAK3X3



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.9	0.7	0.035	0.028
b	0.35	0.24	0.014	0.009
c	0.25	0.1	0.01	0.004
D	3.45	3.05	0.136	0.12
D1	3.2	2.9	0.126	0.114
D2	1.85	1.35	0.073	0.053
E	3.4	3	0.134	0.118
E1	3.25	2.9	0.128	0.114
E2	2.6	2.35	0.102	0.093
e	0.65BSC		0.026BSC	
H	0.5	0.3	0.02	0.012
L	0.5	0.3	0.02	0.012
L1	0.2	0.07	0.008	0.003
ɗ	12Á	0Á	12Á	0Á